

### NOT RECOMMENDED FOR NEW DESIGN **USE DMP56D0UFB**



DMP57D5UFB

#### P-CHANNEL ENHANCEMENT MODE MOSFET

#### **Features**

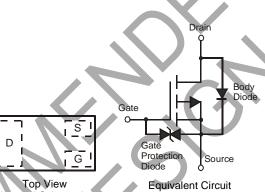
Low On-Resistance:

 $R_{DS(ON)} \le 6\Omega$  @  $V_{GS} = -4.0V$  $R_{DS(ON)} \le 8\Omega$  @  $V_{GS} = -2.5V$ 

- Very Low Gate Threshold Voltage, ≤ 1.0V
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Gate, 1KV**
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

## **Mechanical Data**

- Case: DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.001 grams (approximate)



#### DFN1006-3



**ESD PROTECTED TO 1kV** 



**Bottom View** 

Internal Schematic

## **Ordering Information** (Note 3)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMP57D5UFB-7	DP	7	8	3000
DMP57D5UFB-7B	DP	7	8	10,000

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
- 3. For packaging details, go to our website at http://www.diodes.com.

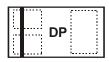
# **Marking Information**

### DMP57D5UFB-7



Top View **Dot Denotes** Drain Side

### DMP57D5UFB-7B



Top View Bar Denotes Gate and Source Side

DP = Product Type Marking Code

DMP57D5UFB Document number: DS31274 Rev. 6 - 3 1 of 5

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## Maximum Ratings @TA = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	-50	V
Gate-Source Voltage			V <sub>GSS</sub>	±8	V
Drain Current (Note 4)	Steady	T <sub>A</sub> = 25°C	I <sub>D</sub>	-200	mA
Pulsed Drain Current (Note 5)			I <sub>DM</sub>	-700	mA

## **Thermal Characteristics**

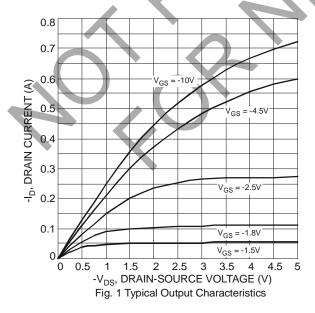
		_	
Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 4)	P <sub>D</sub>	425	mW
Thermal Resistance, Junction to Ambient @T <sub>A</sub> = 25°C (Note 4)	$R_{ hetaJA}$	294	°C/W
Operating and Storage Temperature Range	$T_{J}, T_{STG}$	-55 to +150	°C

## Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)	_					
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-50		_		$V_{GS} = 0V, I_D = -250 \mu A$
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_ `		-10	μА	$V_{DS} = -50V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	7	7	±500	nA	$V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)	•					
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.7	<u> </u>	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	14.	4.6	6 8	Ω	$V_{GS} = -4.0V, I_D = -100mA$ $V_{GS} = -2.5V, I_D = -80mA$
Forward Transfer Admittance	Y <sub>fs</sub>	100		Y	mS	$V_{DS} = -5V, I_D = -100 \text{mA}$
Diode Forward Voltage (Note 6)	V <sub>SD</sub>	_		-1.2	V	$V_{GS} = 0V, I_{S} = -100mA$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C <sub>iss</sub>		29	_	pF	., ., ., ., .,
Output Capacitance	Coss	1	7.3	_	pF	$V_{DS} = -4V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>		2.5	_	pF	T = T.UIVII IZ

Notes:

- Device mounted on FR-4 PCB. t ≤5 sec.
   Pulse width ≤10μS, Duty Cycle ≤1%.
   Short duration pulse test used to minimize self-heating effect



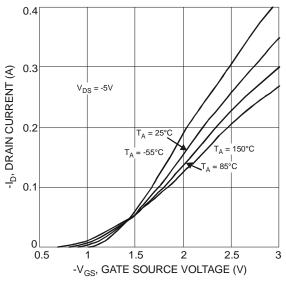


Fig. 2 Typical Transfer Characteristics



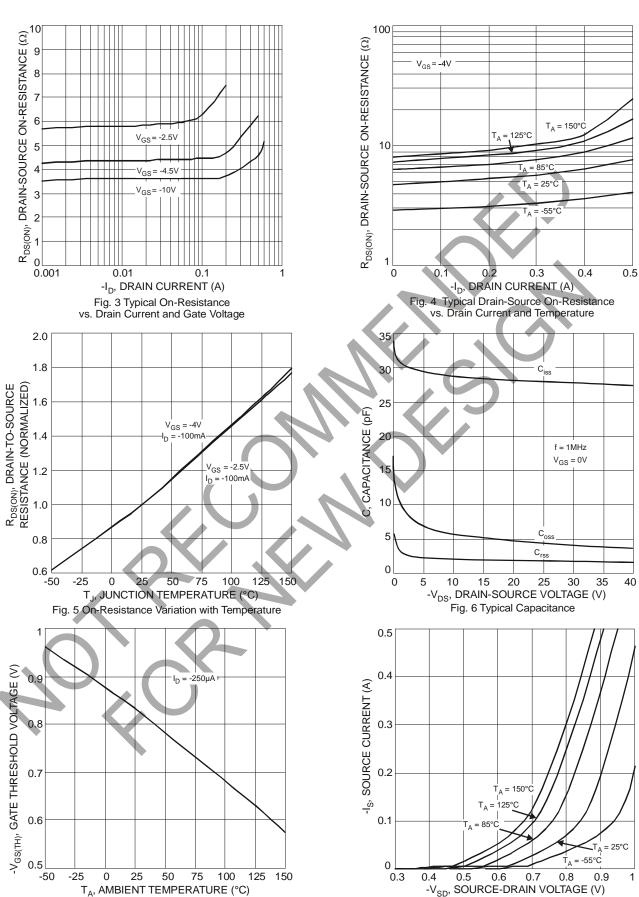
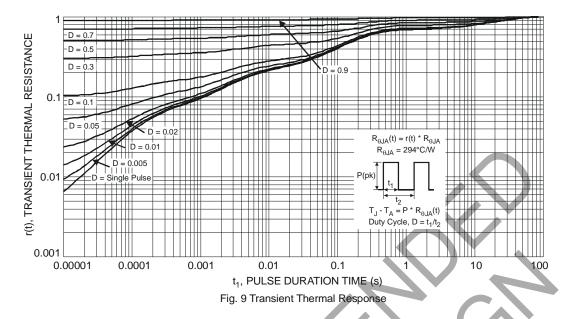


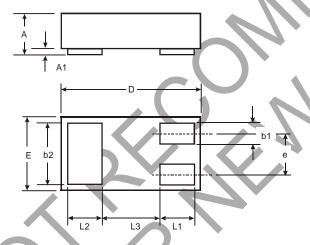
Fig. 7 Gate Threshold Variation vs. Ambient Temperature

Fig. 8 Diode Forward Voltage vs. Current



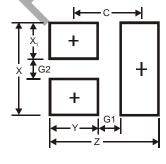


# **Package Outline Dimensions**



DFN1006-3					
Dim	Min	Max	Тур		
Α	0.47	0.53	0.50		
A1	0	0.05	0.03		
b1	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.075	1.00		
Е	0.55	0.675	0.60		
е			0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3			0.40		
All Dimensions in mm					

# **Suggested Pad Layout**



Dimensions	Value (in mm)	
Z	1.1	
G1	0.3	
G2	0.2	
Х	0.7	
X1	0.25	
Y	0.4	
С	0.7	



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